EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20050208322"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:12
L2	521	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:42
L3	20	crystal defect same evaluat$3 same reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
L4	451	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
L5	269	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
L6	45	defect and (evaluat$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
L7	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43

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L8	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:44
L9	35	L8 and etch$3 and crystal with defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
L10	6	selective$2 with etch$3 same crystal defect same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
L11	15	defect same etch$3 and evaluat$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
L12	4	crystal defect same (secco or sertl or wright) with etch$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S1	38	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:31
S2	21	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45
S3	32	first near solution with (hf or "nh. sub.4f") and second near solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45

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S4	1	deffect same etch$3 and evaluat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S5	3124	defect same etch$3 and evaluat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S6	551	defect same etch$3 and evaluat$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S7	13	defect same etch$3 and evaluat$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S8	4	defect same etch$3 same evaluat$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:46
S9	103	defect same etch$3 same evaluat$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:24
S10	26	crystal defect same etch$3 same evaluat$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:42
S11	252	crystal defect and (secco or sertl or wright) with etch$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:43

S12	42	crystal defect same (secco or sertl or wright) with etch$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:45
S13	4	crystal defect same (secco or sertl or wright) with etch$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S14	4	crystal defect and (secco or sertl or wright) with etch$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
S15	4	crystal defect and (secco or sertl or wright) same etch$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
S16	1	crystal defect and evalut$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
S17	0	crystal defect and evalutuat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
S18	2209	crystal defect and evaluat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
S19	16	crystal defect same evaluat$3 same reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43

S20	0	crystal defect same evaluat$3 same reference wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:07
S21	1	crystal defect same evaluat$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
S22	1	crystal defect and evaluat$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
S23	4	crystal defect and evaluat$3 and reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:12
S24	448	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:42
S25	418	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S26	253	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 09:02
S27	0	("crystaldefectandhfwithconcentration").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 09:03

S28	154	crystal defect and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:38
S29	39	crystal defect and evaluat$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:03
S30	1	crystal defect and evaluat$3 and hf with concentration and defect free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
S31	1	crystal defect and evaluat$3 and hf with concentration and defect-free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
S32	39	crystal defect and evaluat$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28
S33	1	crystal defect and evaluat$3 and defect free reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:06
S34	10	crystal defect and evaluat$3 and defect free with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20
S35	0	crystal defect and evaluat$3 and defect free with reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08

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S36	1	crystal defect and evaluat$3 and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S37	1	crystal defect and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S38	185	defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S39	8	defect free and reference image and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S40	2	crystal defect and evaluat$3 and defect free with reference and no defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20
S41	11	crystal defect and evaluat$3 and ((defect free) or (no defect)) with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:21
S42	47	crystal defect and (evaluat$3 or detection) and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28
S43	1	crystal defect and (evaluat$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30

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S44	1	crystal defect and (evaluat$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30
S45	36	defect and (evaluat$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
S46	0	defect and (evaluat$3 or detection) same hydroflouric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
S47	220	defect and (evaluat$3 or detection) and hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
S48	12	defect and (evaluat$3 or detection) same hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:08
S49	58	crystal defect and (evaluat$3 or detection) same hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:09
S50	1	crystal defect and (evaluat$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:10
S51	10	crystal defect same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:35

S52	152	ultrasonic wave same etch$3 same clean$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S53	23	ultrasonic wave same etch$3 same clean$3 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S54	45	ultrasonic wave same etch$3 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S55	13	ultrasonic wave same etch$3 same known same clean$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S56	2	("20050208322").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 10:18
S57	167	crystal defect and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:38
S58	2	"20050208322"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:43
S59	10	etch$3 same crystal defect and device pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 19:49

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S60	257	etch$3 same crystal defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 19:49
S61	44	selective$2 with etch$3 same crystal defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:07
S62	6	selective$2 with etch$3 same crystal defect same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S63	0	("257e21.53").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/08 20:27
S64	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S65	61	S64 and etch$3 and crystal with defect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:30
S66	49	S64 and etch$3 and crystal with defect and pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:30

S67	35	S64 and etch$3 and crystal with defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S68	3	S64 and crystal with defect and etch$3 same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:36